



Extended Common Mode LVDS Solutions

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***20th SpaceWire
Working Group
meeting***

2013, April 10th, 16:40 – 17:00

Outline



- Last Meeting State
- Measurement Results
- Components Development
- Features Development
- Radiation Test Results
- Conclusion

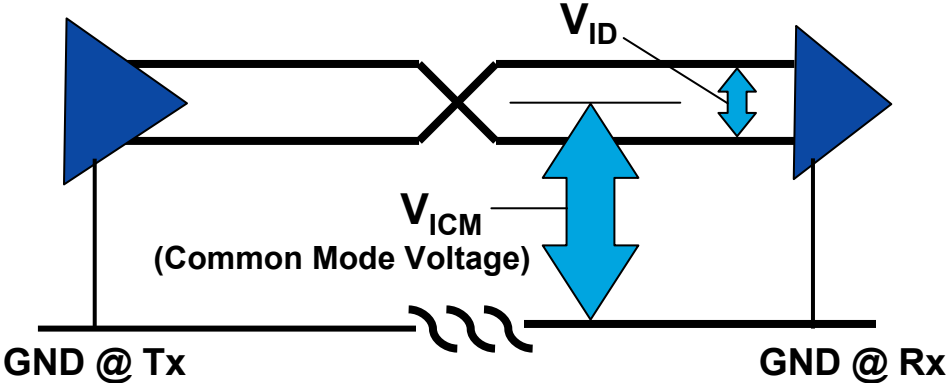
Last Meeting State

TELEFUNKEN Semiconductors Extended Common Mode LVDS

- SOI technologies: 0.35 μ m, 0.8 μ m
 - robustness: ≤ 200 V, no Latch-Up
 - efficiency: LV & HV on die, 0.8 μ m isolation ≤ 100 V
 - suitable for harsh and radiation environments
- Competitive high-speed performance and efficiency of LVDS
- Robustness of RS-485/422
- Common mode rejection to be measured
- Failsafe to be improved
- Cold spare capability to be improved
- Further radiation tests to be done

Extended Common Mode Measurements

Data Rate (PRBS23) = 200Mbps, $V_{ID} = 200\text{mV}$, V_{ICM} settings:



12V

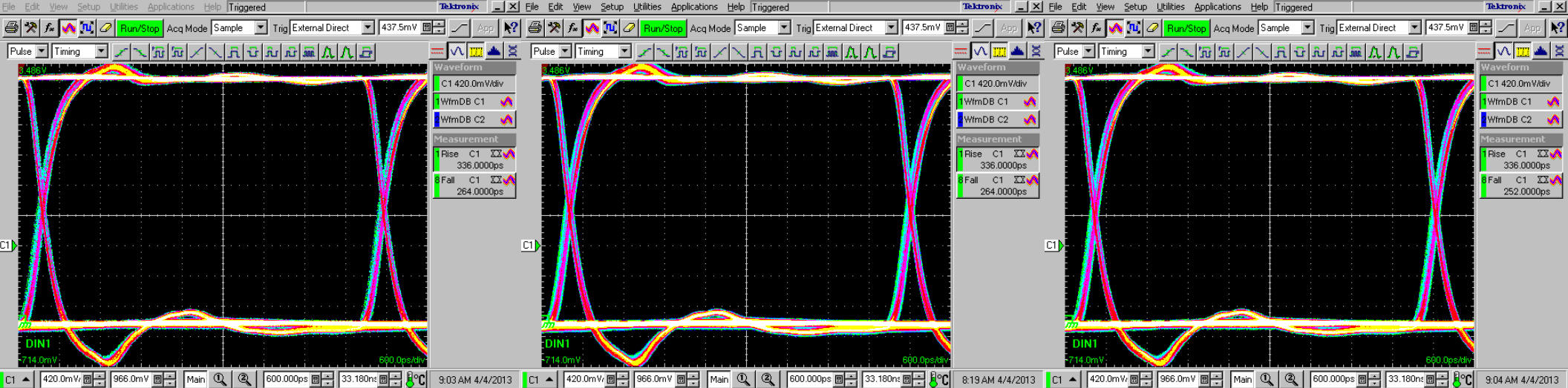
1.2V

-7V

$V_{ICM} = -7\text{V}$

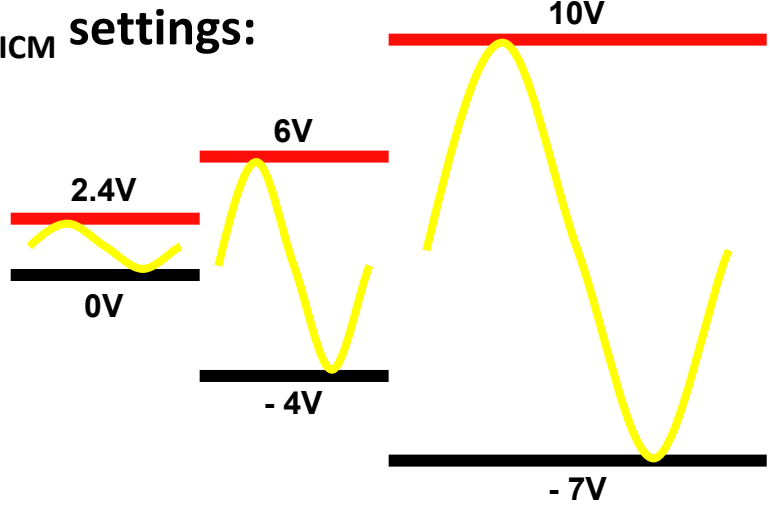
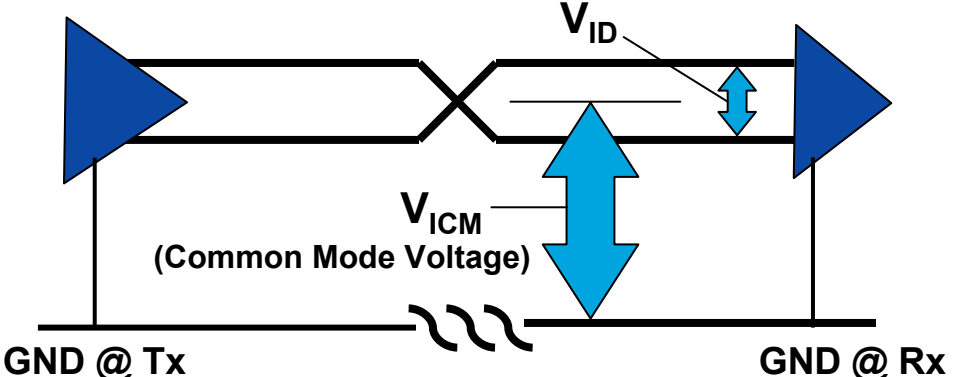
$V_{ICM} = 1.2\text{V}$

$V_{ICM} = 12\text{V}$



Extended Common Mode Measurements (2)

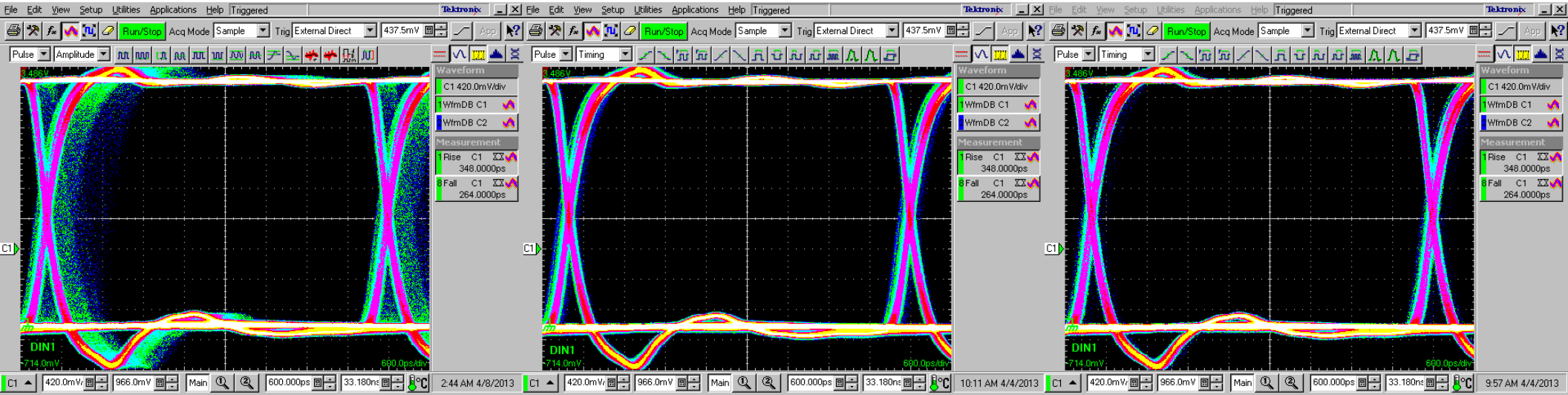
Data Rate (PRBS23) = 200Mbps, $V_{ID} = 200mV$, V_{ICM} settings:



$0V \leq V_{ICM} \leq 2.4V$, $f = 2kHz$

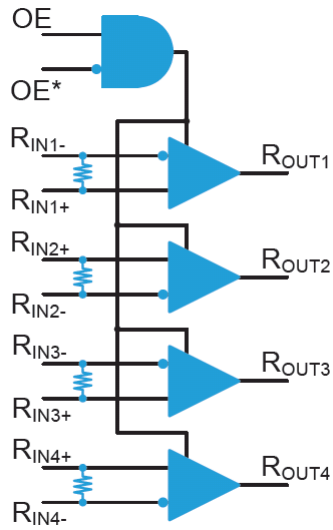
$-4V \leq V_{ICM} \leq 6V$, $f = 250Hz$

$-7V \leq V_{ICM} \leq 10V$, $f = 150Hz$

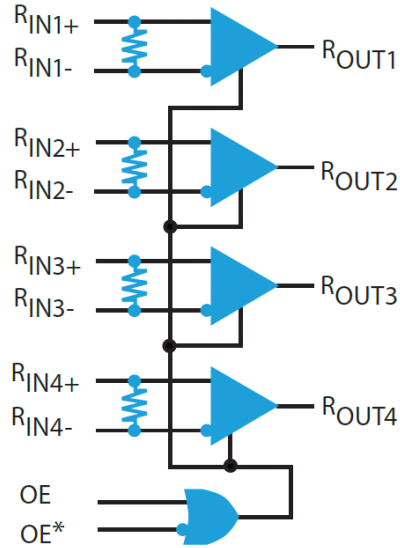


Introduced Components

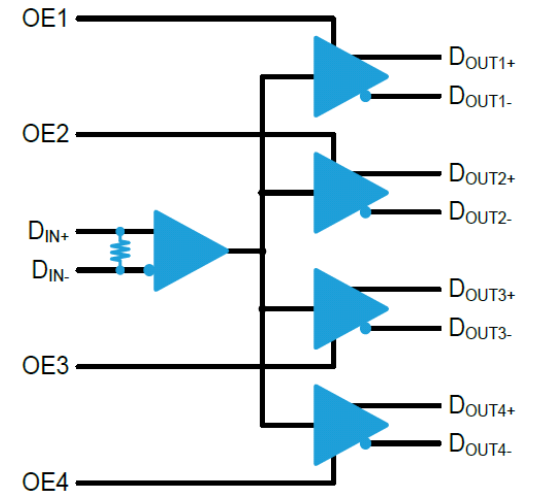
TF90LVDS048



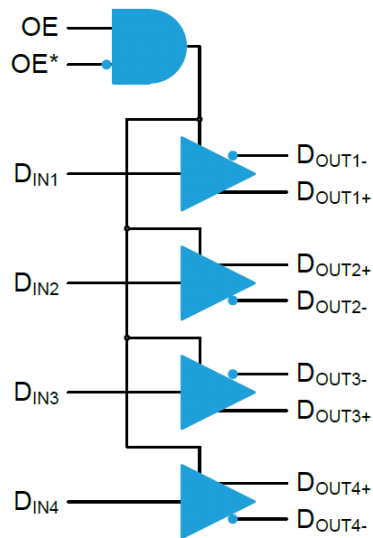
TF90LVDS032



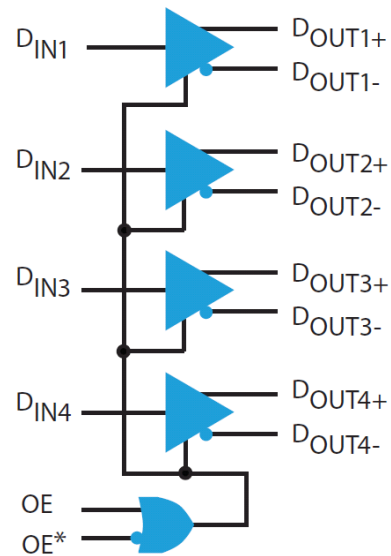
TF90LVDS104



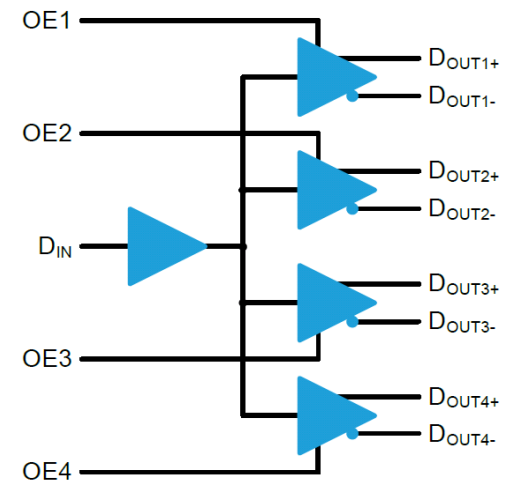
TF90LVDS047



TF90LVDS031

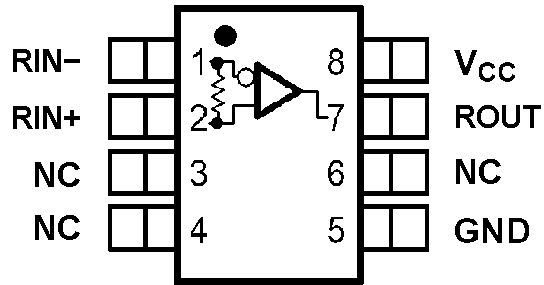


TF90LVDS105

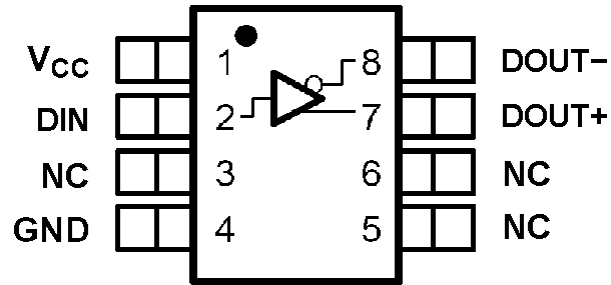


Future Components

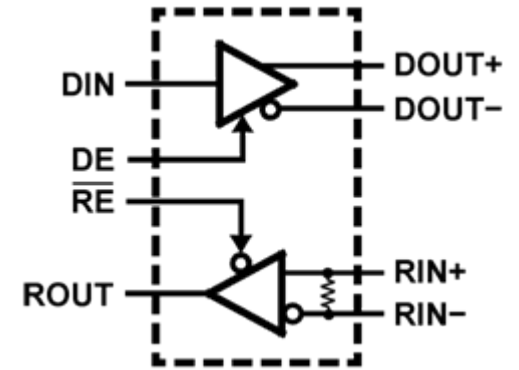
TF90LVDS018



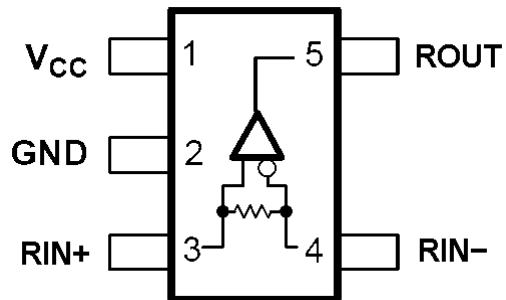
TF90LVDS017



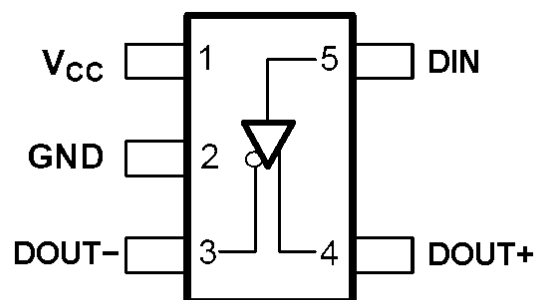
TF90LVDS019



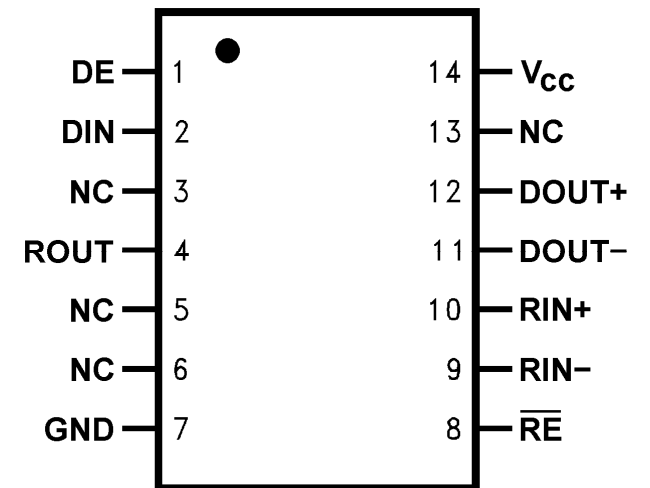
TF90LVDS012



TF90LVDS011

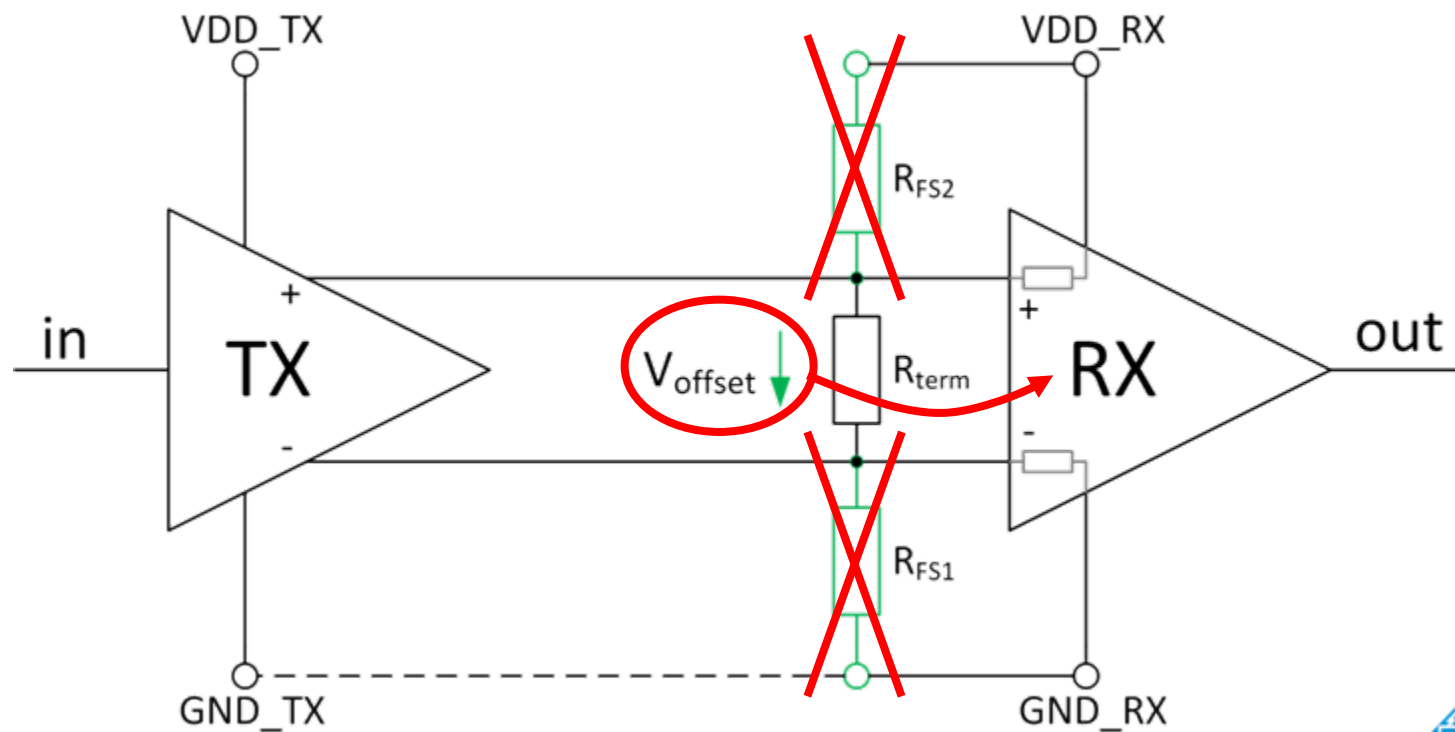


TF90LVDS019



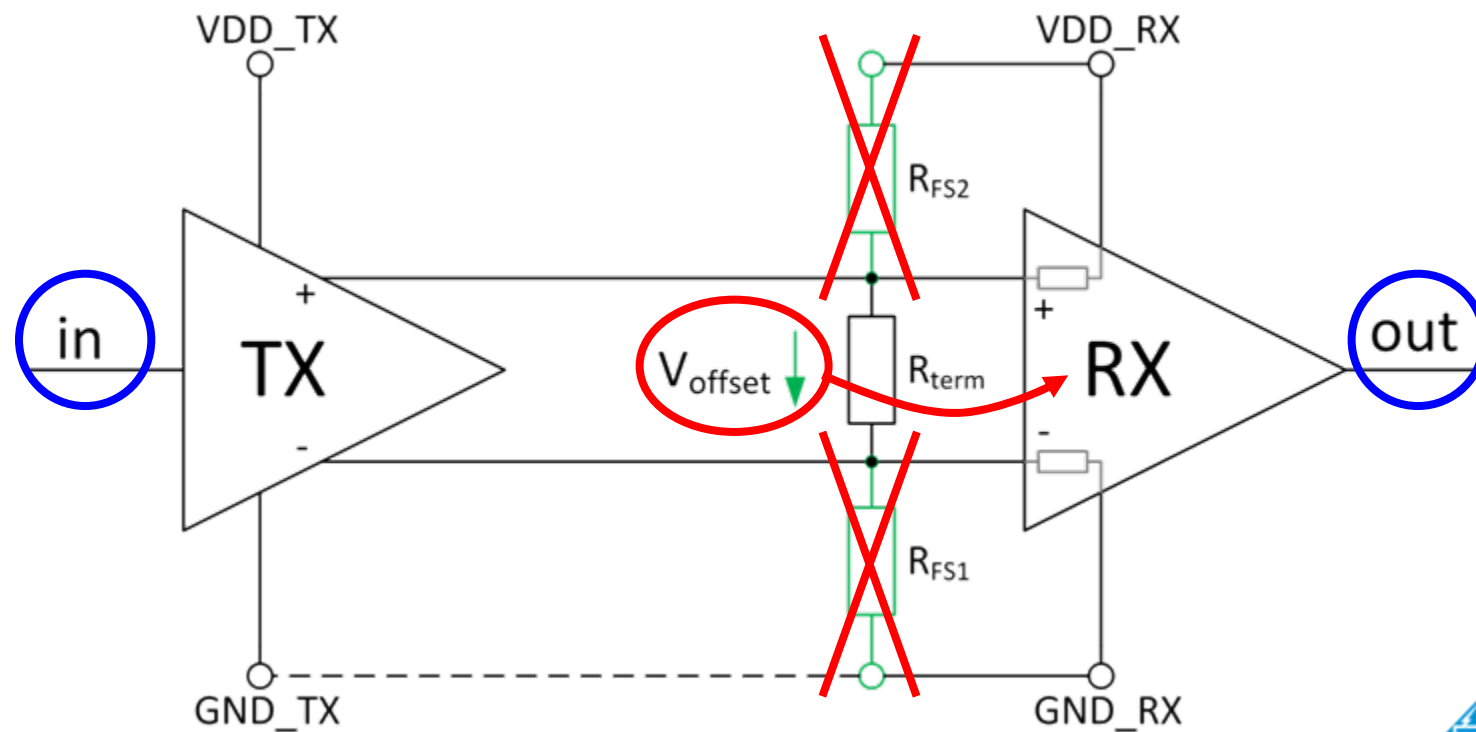
Improved Features

- Failsafe Functionality
 - implement feature in the receiver
- Cold Spare Capability



Improved Features

- Failsafe Functionality
- Cold Spare Capability
 - available on LVDS side
 - implement feature on CMOS side



Preliminary TID Radiation Test

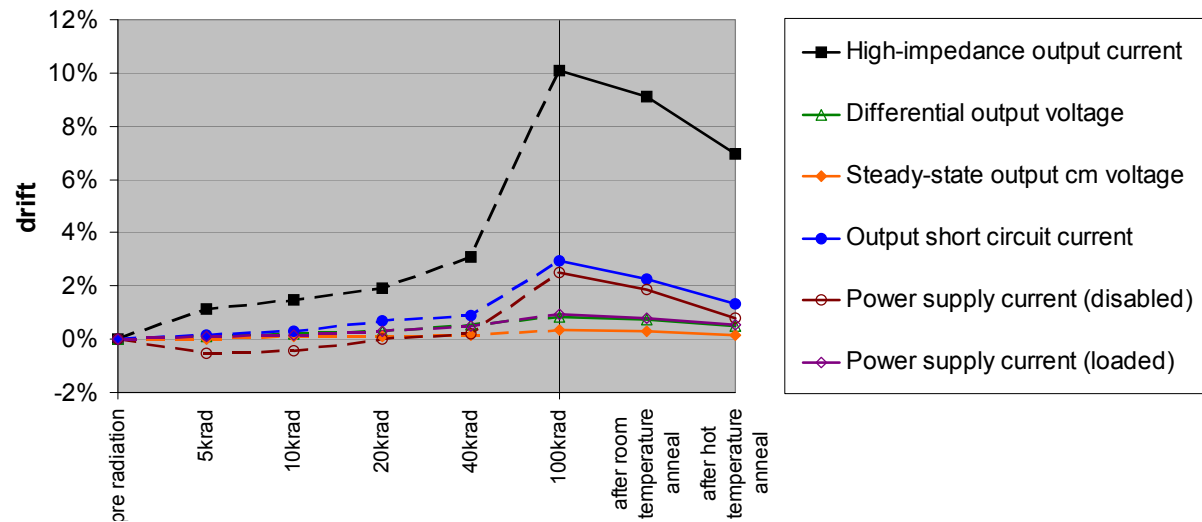
Conditions

- TID without applied bias
- 5 TID groups
- Dose rate: 75 rad/min (^{60}Co source)
- Room temperature annealing
- Hot temperature annealing
100°C for 5 h

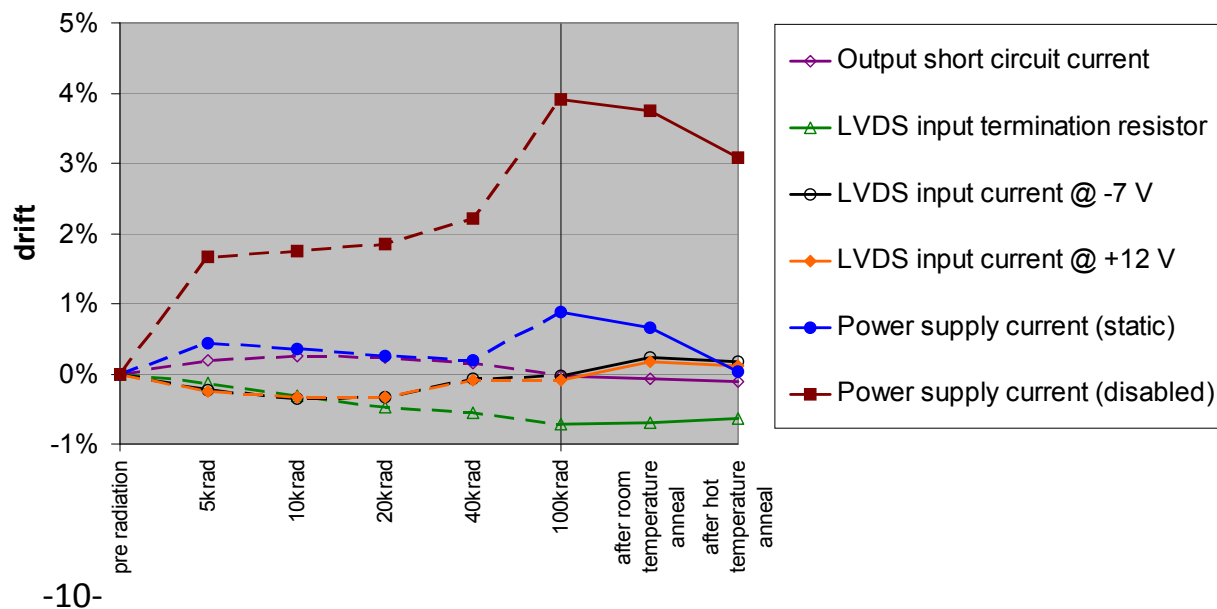
Results

- Minor shifts in key data sheet parameters after TID irradiation up to 100krad
- None of the component specifications are violated
 - all tested parts keep their complete functionality

TF90LVDS031



TF90LVDT032



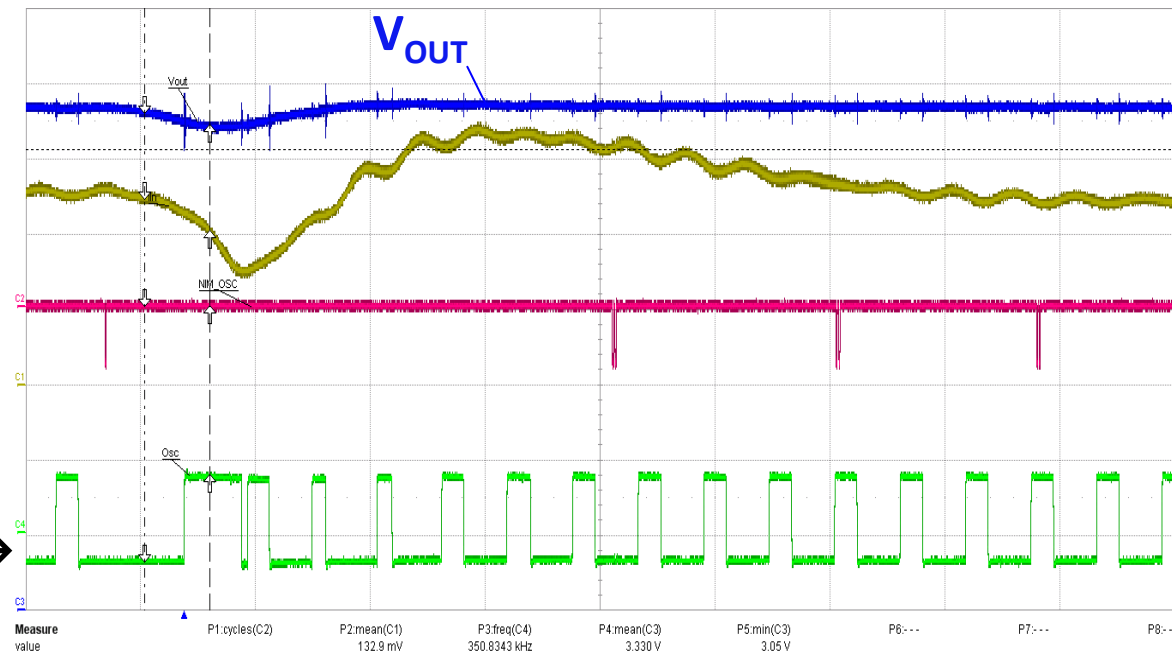
New Results: SEE Heavy Ions Test

LVDS Receiver & Driver

- SEE test is being prepared and will follow very soon

Point-of-Load Converter

- same technology as LVDS components
- utilizing all technology devices used in LVDS components
- $V_{IN} \leq 26V$, $I_{OUT} \leq 3A$
- SEE 60.7MeV/(mg/cm²): **no fails**; SET →



Acknowledgement

- Many thanks to ESA/ESTEC for preparing and performing the SEE tests:
 - Giorgio Magistrati
 - Gianluca Furano
 - Farid Guettache

Conclusion

- Extended Common Mode LVDS is still challenging application
- The components from TELEFUNKEN Semiconductors are showing good common mode rejection
 - High frequency CM-noise have to be filtered
- TELEFUNKEN Semiconductors is testing new features
 - Improved failsafe functionality
 - Full cold spare capability
- Radiation tests
 - Good results until now
 - SEE test of LVDS will follow
 - TID test with applied bias will follow



***Thank you for your
attention!***